

100 V, 3A PNP high power bipolar transistor 13 January 2014

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61003NY

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Loadswitch

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- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

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T. I. I. A.

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-100	V
I _C	collector current		-	-	-3	А
I _{CM}	peak collector current	$t_p \le 1 \text{ ms}$; single pulse	-	-	-8	А
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	110	180	mΩ



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	mb	C .
2	E	emitter		в
3	E	emitter		ľ~
4	В	base	មូចូត្	E sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PHPT61003PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT61003PY	1003PAB

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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

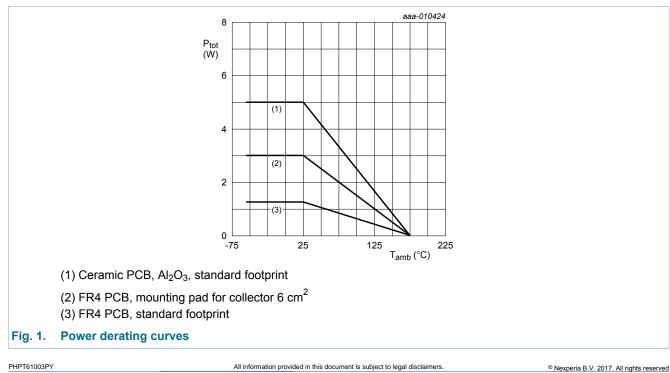
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-100	V
V _{CEO}	collector-emitter voltage	open base		-	-100	V
V _{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-3	А
I _{CM}	peak collector current	$t_p \le 1 \text{ ms}$; single pulse		-	-8	А
I _B	base current			-	-0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated mounting pad for collector 6 cm².

[3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.

[4] Power dissipation from junction to mounting base.

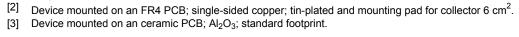


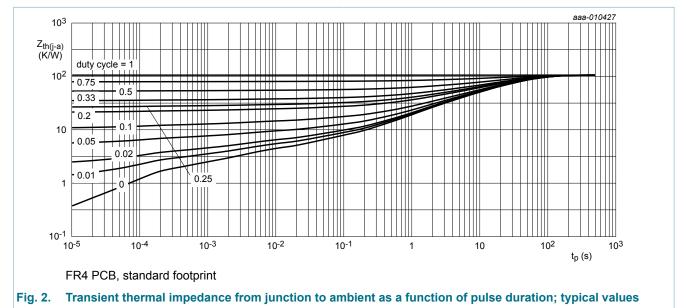
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9. Thermal characteristics

Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W	
			[2]	-	-	50	K/W	
			[3]	-	-	30	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

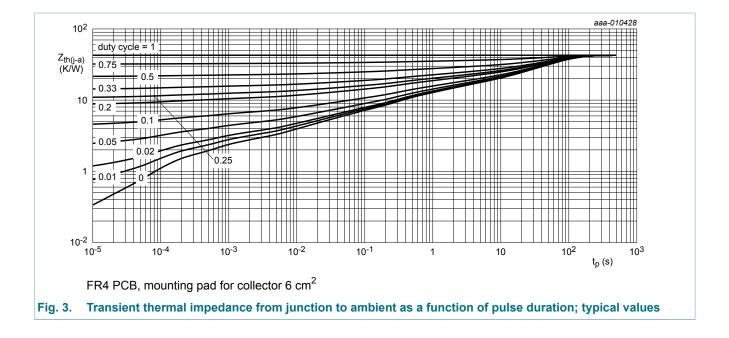




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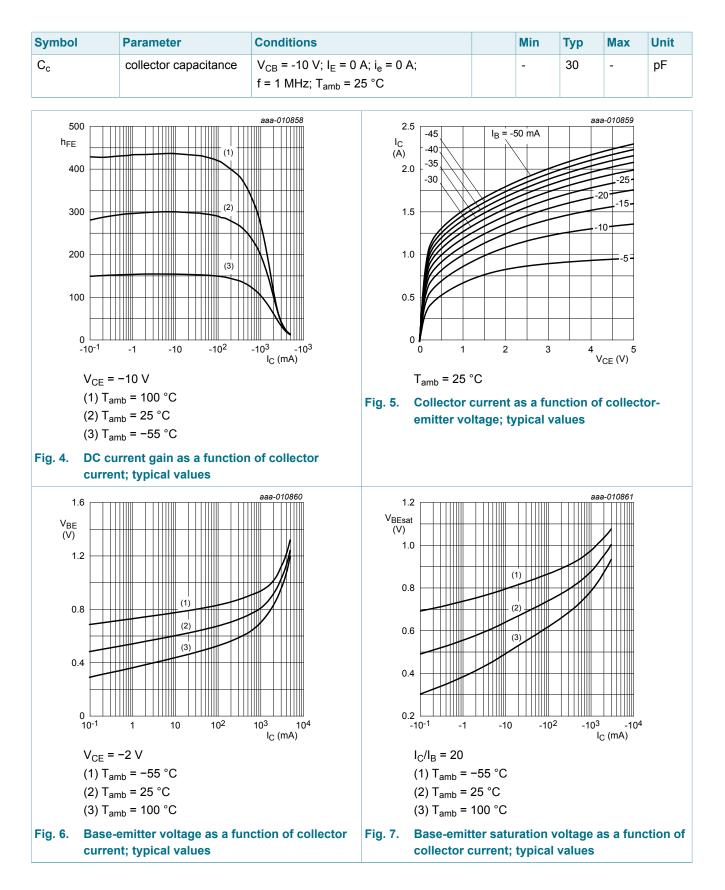
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -80 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -8 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -10 V; I _C = -500 mA; T _{amb} = 25 °C	150	220	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} \texttt{=} \texttt{-10} \; V; \; I_{C} \texttt{=} \texttt{-1} \; A; \; t_{p} \texttt{\leq} \texttt{300} \; \mu \texttt{s}; \\ \\ \bar{D} \texttt{\leq} \texttt{0.02} \; ; \; T_{amb} \texttt{=} \texttt{25} \; ^{\circ} C; \; \texttt{pulsed} \end{array}$	80	210	-	
		$V_{CE} = -10 \text{ V}; \text{ I}_{C} = -2 \text{ A}; \text{t}_{p} \leq 300 \mu\text{s};$ $\delta \leq 0.02 \text{ ; } \text{T}_{amb} = 25 ^{\circ}\text{C}; \text{ pulsed}$	20	100	-	
		V_{CE} = -10 V; I _C = -3 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	10	40	-	
OLOUI	collector-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-70	-110	mV
		$\begin{split} I_{C} &= -2 \text{ A}; I_{B} = -200 \text{ mA}; t_{p} \leq 300 \mu\text{s}; \\ \delta \leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-220	-360	mV
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} I_{C} &= -2 \text{ A}; I_{B} = -200 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	110	180	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-0.91	-1	V
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-1.02	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -100 mA; T _{amb} = 25 °C	-	-0.68	-0.9	V
t _d	delay time	V_{CC} = -12.5 V; I _C = -1 A; I _{Bon} = -50 mA;	-	20	-	ns
tr	rise time	I _{Boff} = 50 mA; T _{amb} = 25 °C	-	180	-	ns
on	turn-on time		-	200	-	ns
s	storage time		-	350	-	ns
t _f	fall time		-	220	-	ns
t _{off}	turn-off time		-	570	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	-	125	-	MHz

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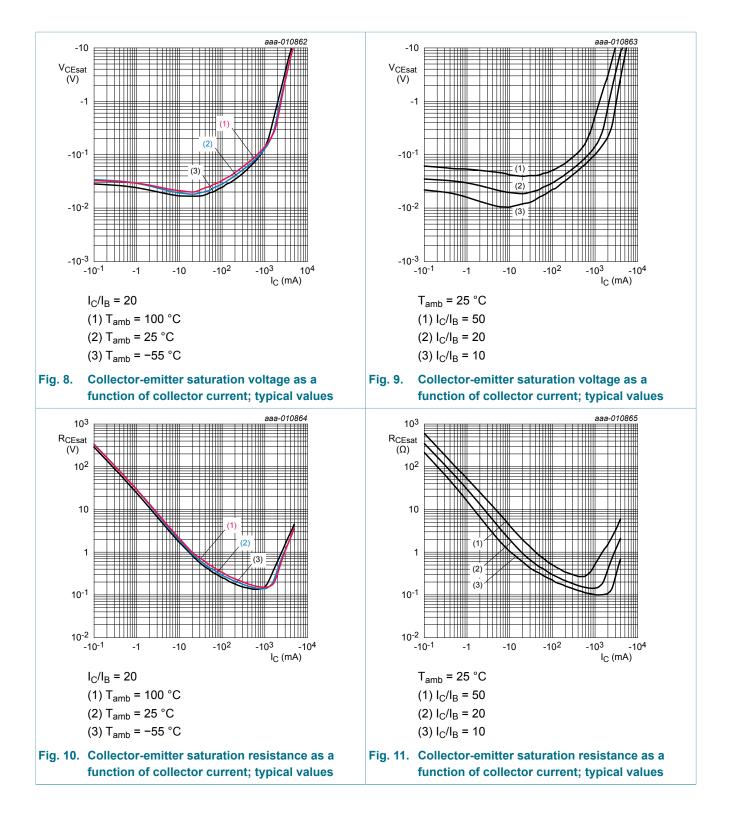
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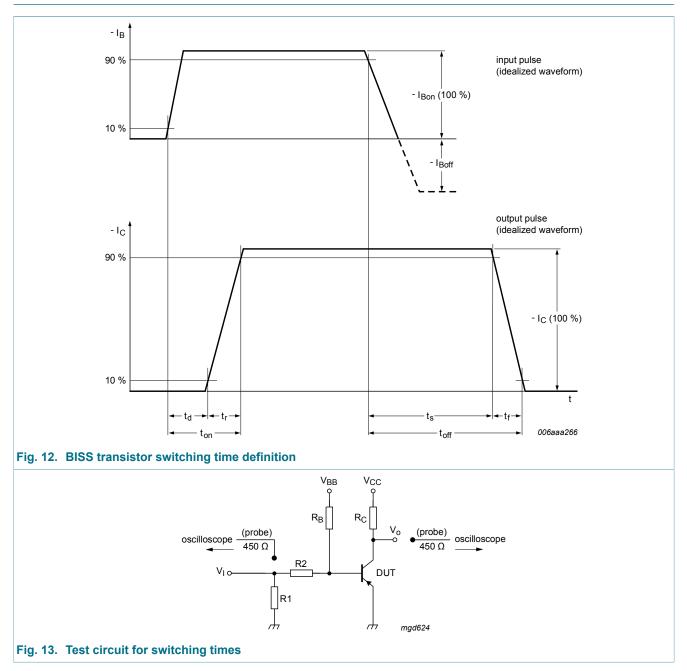
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11. Test information

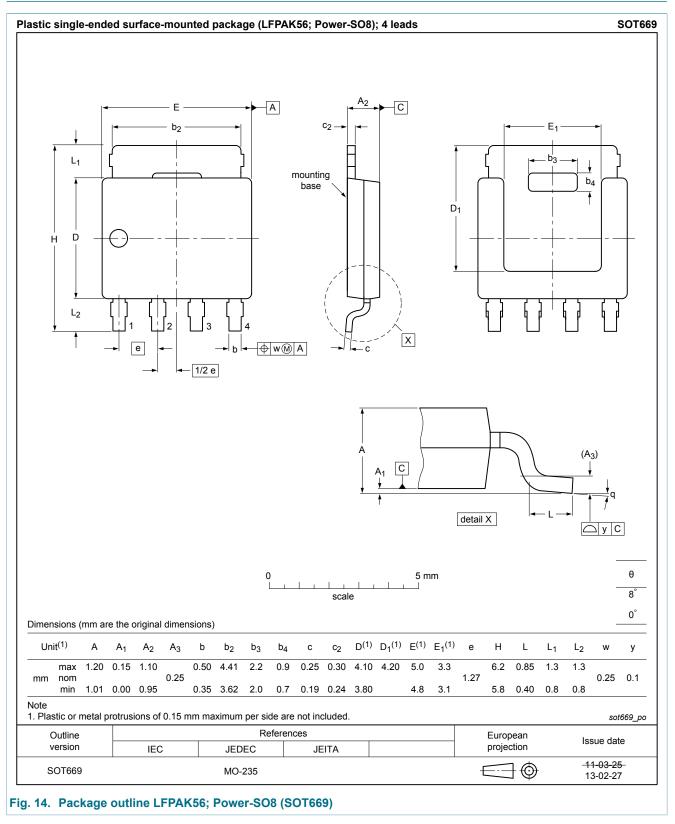
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



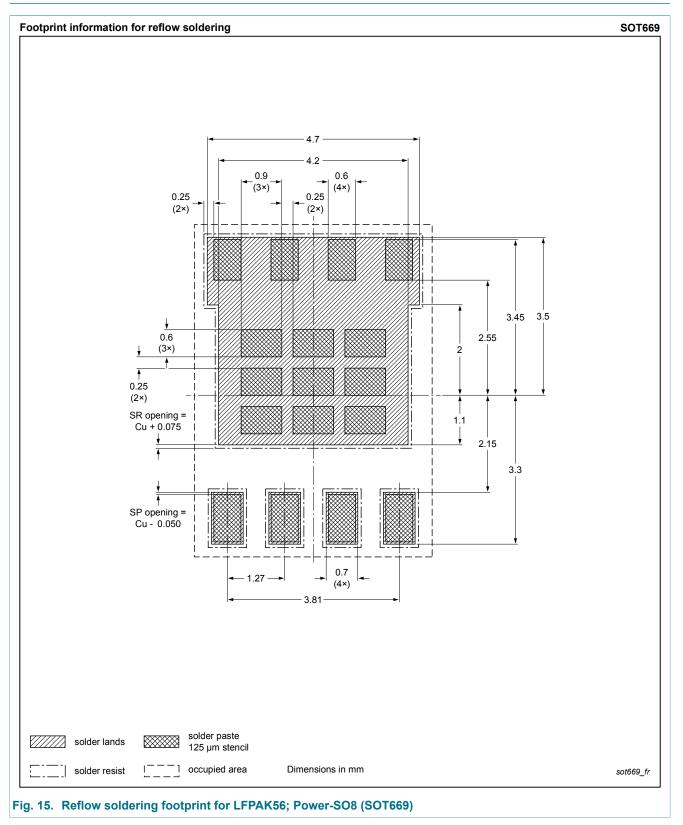
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13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PHPT61003PY v.1	20140113	Product data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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